

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

**Claim 1 (original):** A III nitride single-crystal manufacturing method wherein a liquid layer of 200  $\mu\text{m}$  or less thickness is formed in between a substrate and a III nitride source-material baseplate, and III nitride single crystal is grown onto the face of said substrate on its liquid-layer side.

**Claim 2 (original):** A III nitride single-crystal manufacturing method set forth in claim 1, wherein said substrate in at least a superficial layer along the liquid layer is formed of a III nitride single crystal, and said III nitride source-material baseplate is formed of a III nitride polycrystal.

**Claim 3 (original):** A III nitride single-crystal manufacturing method set forth in claim 1, wherein said substrate in at least a superficial layer along the liquid layer, and said III nitride source-material baseplate are formed of a III nitride single crystal, and the face of said substrate on its liquid-layer side is a Group-III-atom surface; and the face of said III nitride source-material baseplate on its liquid-layer side is a nitrogen-atom surface.

**Claim 4 (currently amended):** A III nitride single-crystal manufacturing method set forth in ~~any of claims~~ claim 1 ~~through 3~~, wherein said liquid layer includes

an element of at least one kind selected from the group consisting of elements constituting said III nitride single crystal.

**Claim 5 (original):** A III nitride single crystal obtained according to the III nitride single-crystal manufacturing method set forth in any of claims 1 through 4.

**Claim 6 (original):** A semiconductor device incorporating the III nitride single crystal set forth in claim 5.